# PMN40UPE

# 20 V, single P-channel Trench MOSFET 13 August 2012

**Product data sheet** 

#### 1. **Product profile**

#### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- Low threshold voltage
- Fast switching
- Trench MOSFET technology
- 4 kV ESD protection

#### 1.3 Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	-6	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -3 A; $T_j$ = 25 °C		-	37	43	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





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# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D I
2	D	drain		
3	G	gate		$G \left( \begin{array}{c} & & & & \\ & & & & \\ & & & & \\ & & & & $
4	S	source	TSOP6 (SOT457)	
5	D	drain		
6	D	drain		S 017aaa259

# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMN40UPE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PMN40UPE	WD

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C; $t \le 5$ s	[1]	-	-6	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-4.7	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-3.5	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	-16	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	500	mW
			[1]	-	1220	mW
		$T_{sp}$ = 25 °C		-	8330	mW

PMN40UPE

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Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.3	Α
ESD maximum rating						
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	4000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

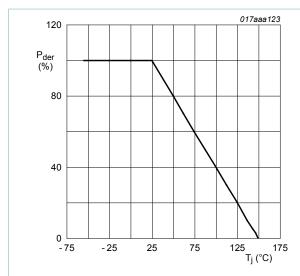


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

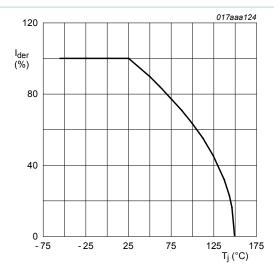


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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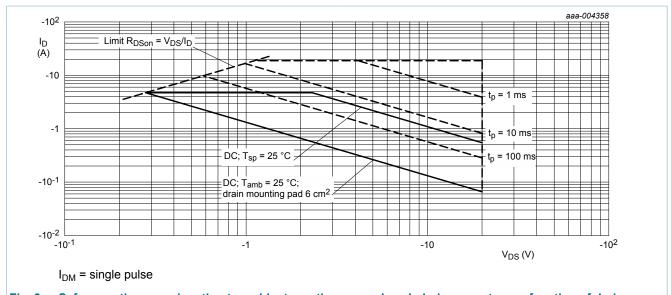


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uiy-a)	thermal resistance		[1]	-	216	250	K/W
	from junction to		<u>[2]</u>	-	83	95	K/W
	ambient	in free air; t ≤ 5 s	<u>[2]</u>	-	51	60	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	10	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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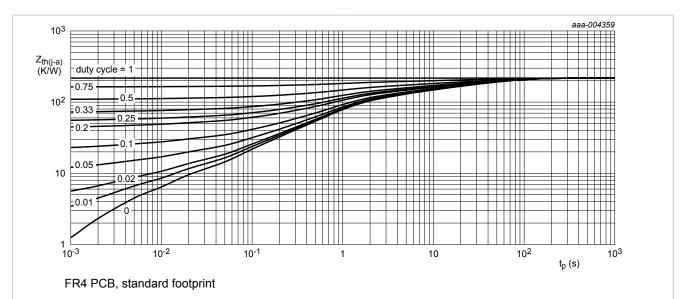


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

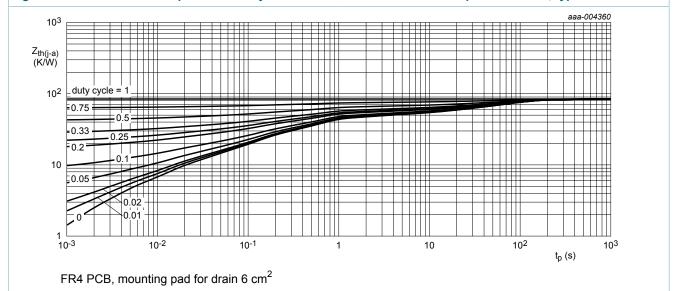


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static chara	Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		-20	-	-	V	
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 °C$		-0.45	-0.7	-0.95	V	
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-	-	-1	μΑ	
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>amb</sub> = 150 °C		-	-	-15	μΑ	
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -3 A; $T_j$ = 25 °C	-	37	43	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_D$ = -3 A; $T_j$ = 150 °C	-	51	59	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -3 A; $T_j$ = 25 °C	-	45	55	mΩ
		$V_{GS}$ = -1.8 V; $I_D$ = -3 A; $T_j$ = 25 °C	-	59	72	mΩ
9fs	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -4 A; $T_{j}$ = 25 °C	-	15	-	S
Dynamic cl	haracteristics					,
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -4.4 A; $V_{GS}$ = -4.5 V; $T_{j}$ = 25 °C	-	15.6	23	nC
$Q_{GS}$	gate-source charge		-	2.5	-	nC
$Q_{GD}$	gate-drain charge		-	2.8	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = -10 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	1820	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	207	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	146	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -4 A; $V_{GS}$ = -4.5 V;	-	8	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	21	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	50	-	ns
t <sub>f</sub>	fall time		-	34	-	ns
Source-dra	in diode		I		1	
$V_{SD}$	source-drain voltage	$I_S = -1.2 \text{ A}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-	-0.7	-1.2	V

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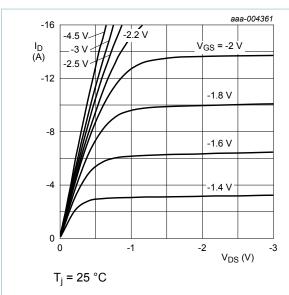
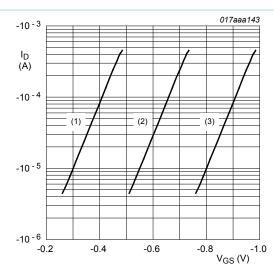


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_j$$
 = 25 °C;  $V_{DS}$  = -3  $V$ 

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

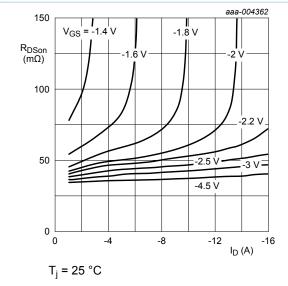


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

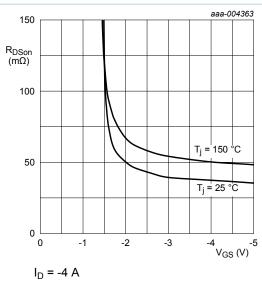


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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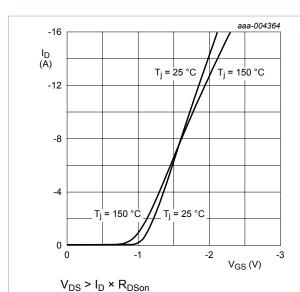


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

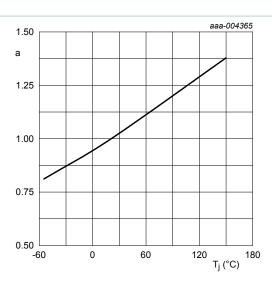


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

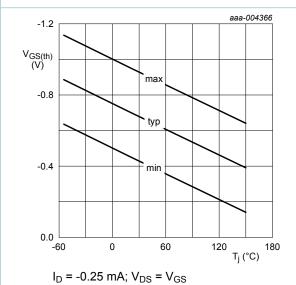


Fig. 12. Gate-source threshold voltage as a function of junction temperature

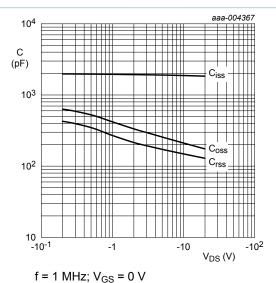


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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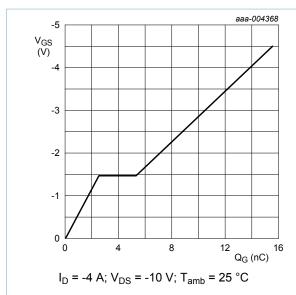


Fig. 14. Gate-source voltage as a function of gate charge; typical values

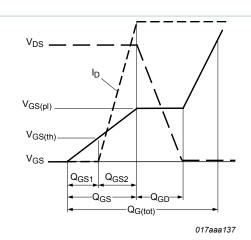


Fig. 15. Gate charge waveform definitions

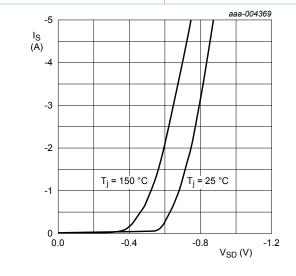
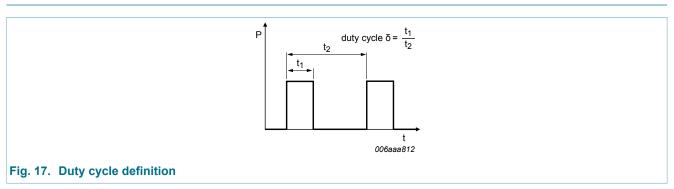


Fig. 16. Source current as a function of source-drain voltage; typical values

## 8. Test information

 $V_{GS} = 0 V$ 



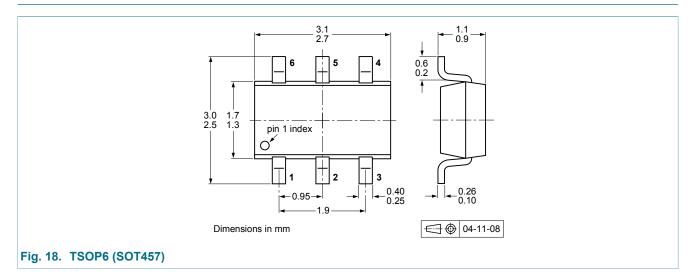
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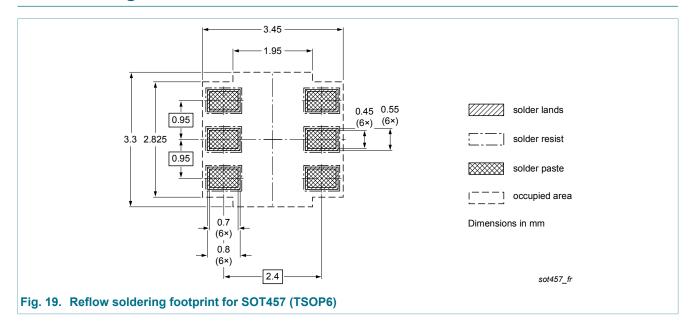
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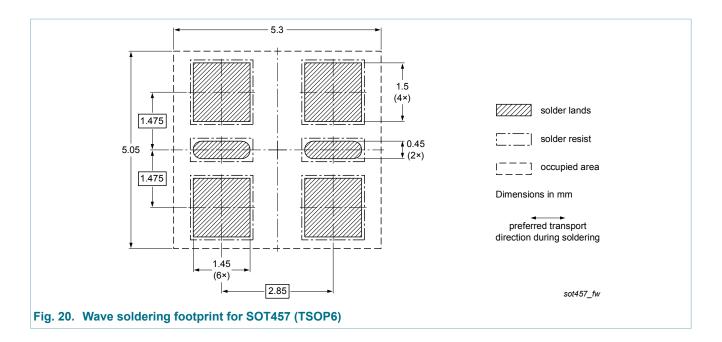
## 9. Package outline



## 10. Soldering



#### 20 V, single P-channel Trench MOSFET



# 11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN40UPE v.1	20120813	Product data sheet	-	-

#### 20 V, single P-channel Trench MOSFET

### 12. Legal information

#### 12.1 Data sheet status

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